



# YJQ200P10AJ

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## P-Channel Enhancement Mode Field Effect Transistor

### Product Summary

$V_{DS}$	-100V
$I_D$	-8A
$R_{DS(ON)}$ ( at $V_{GS}=-10V$ )	200m
$R_{DS(ON)}$ ( at $V_{GS}=-4.5V$ )	235m
100% EAS Tested	
100% $V_{DS}$ Tested	

### General Description

Excellent package for heat d(e)llent package fo100%



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## Electrical Characteristics ( $T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
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## Typical Electrical and Thermal Characteristics Diagrams

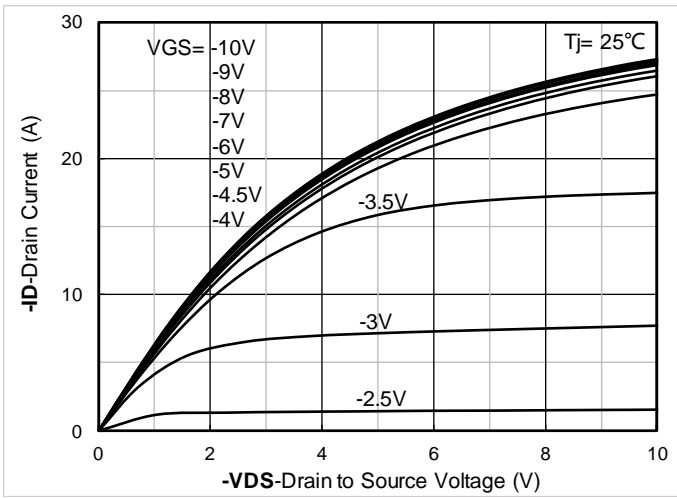


Figure 1. Output Characteristics

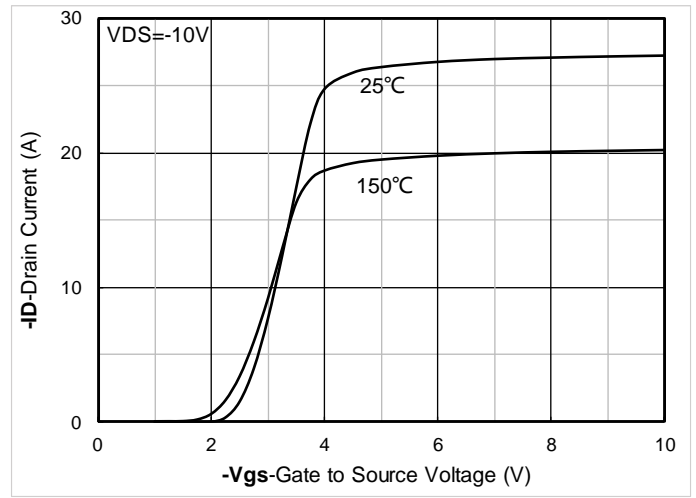


Figure 2. Transfer Characteristics

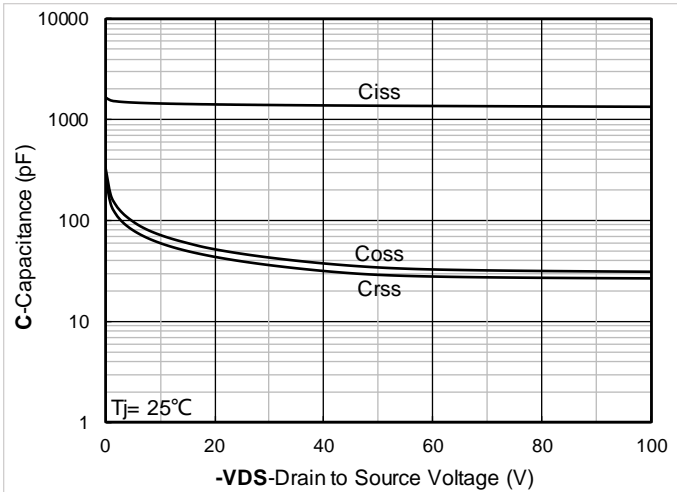


Figure 3. Capacitance Characteristics

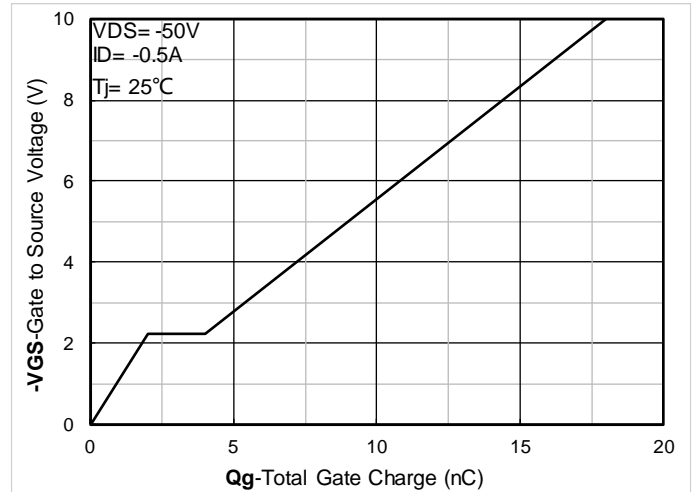


Figure 4. Gate Charge

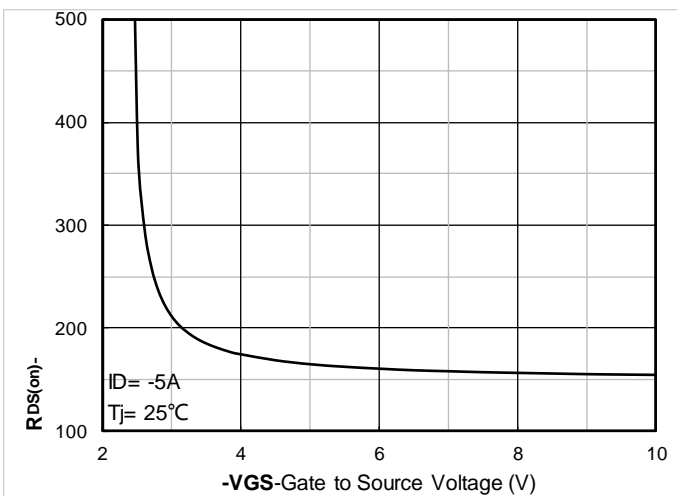


Figure 5. On-Resistance vs Gate to Source Voltage

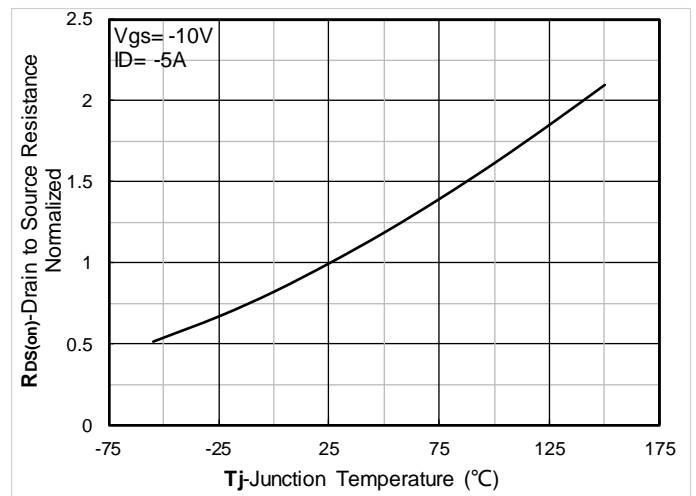


Figure 6. Normalized On-Resistance



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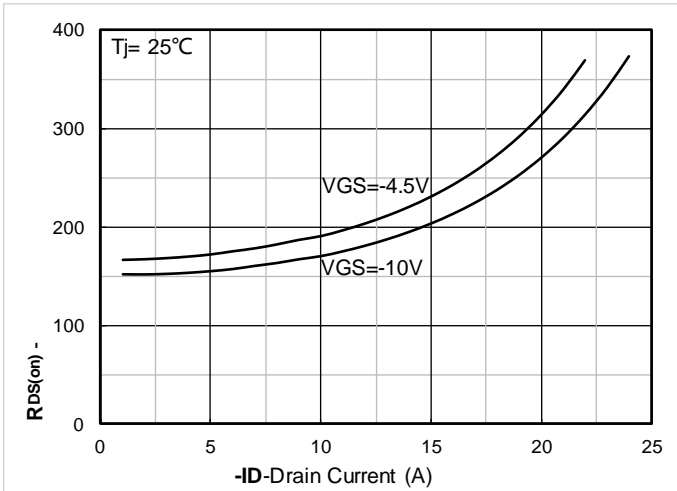


Figure 7. RDS(on) VS Drain Current

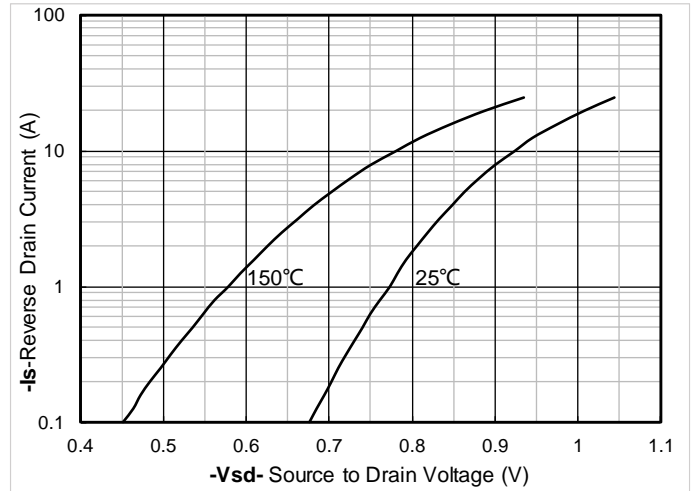


Figure 8. Forward characteristics of reverse diode

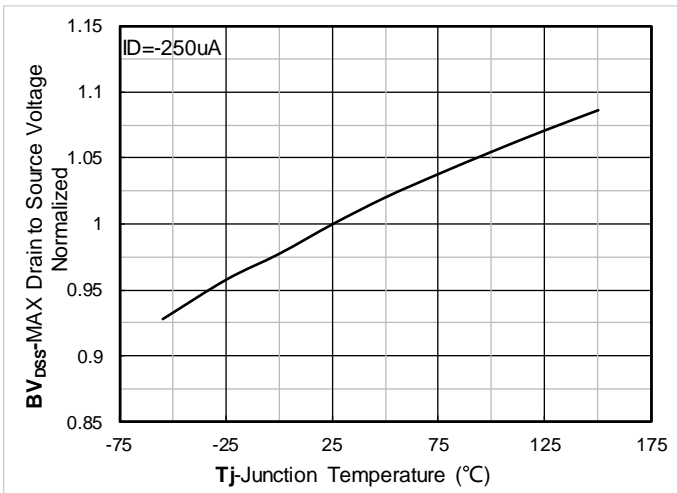


Figure 9. Normalized breakdown voltage

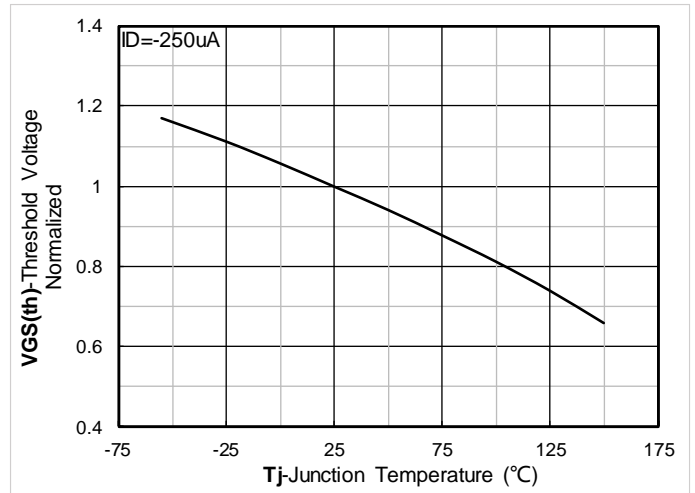


Figure 10. Normalized Threshold voltage

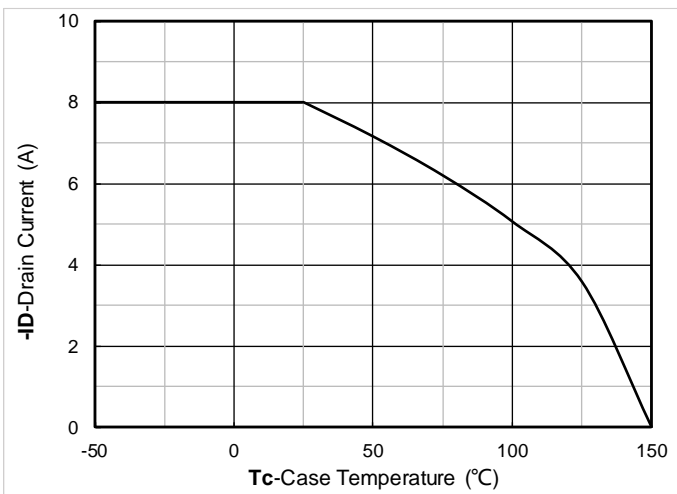


Figure 11. Current dissipation

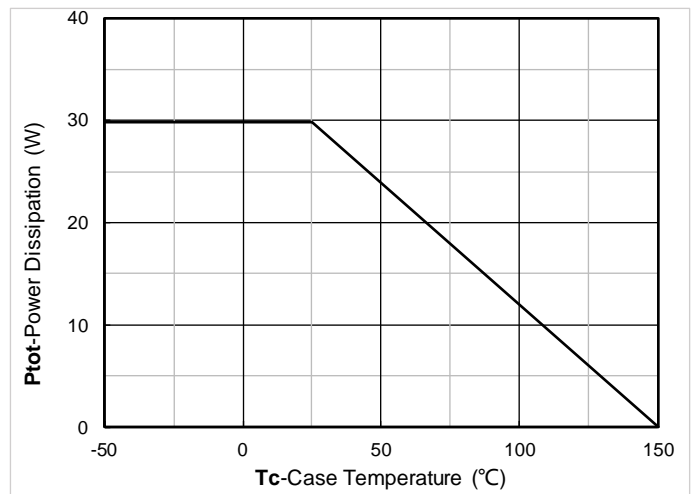


Figure 12. Power dissipation



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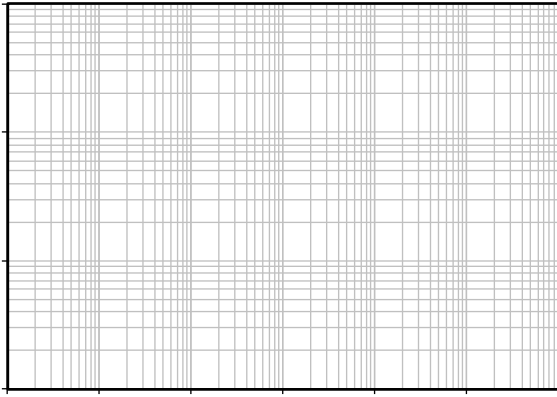


Figure 13. Maximum Transient Thermal Impedance

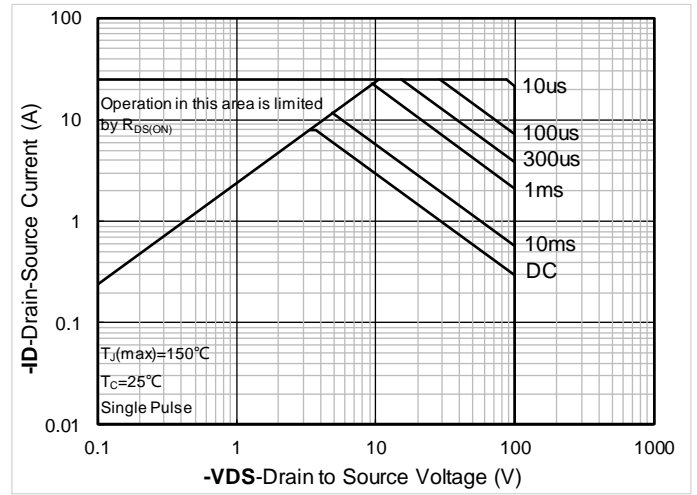
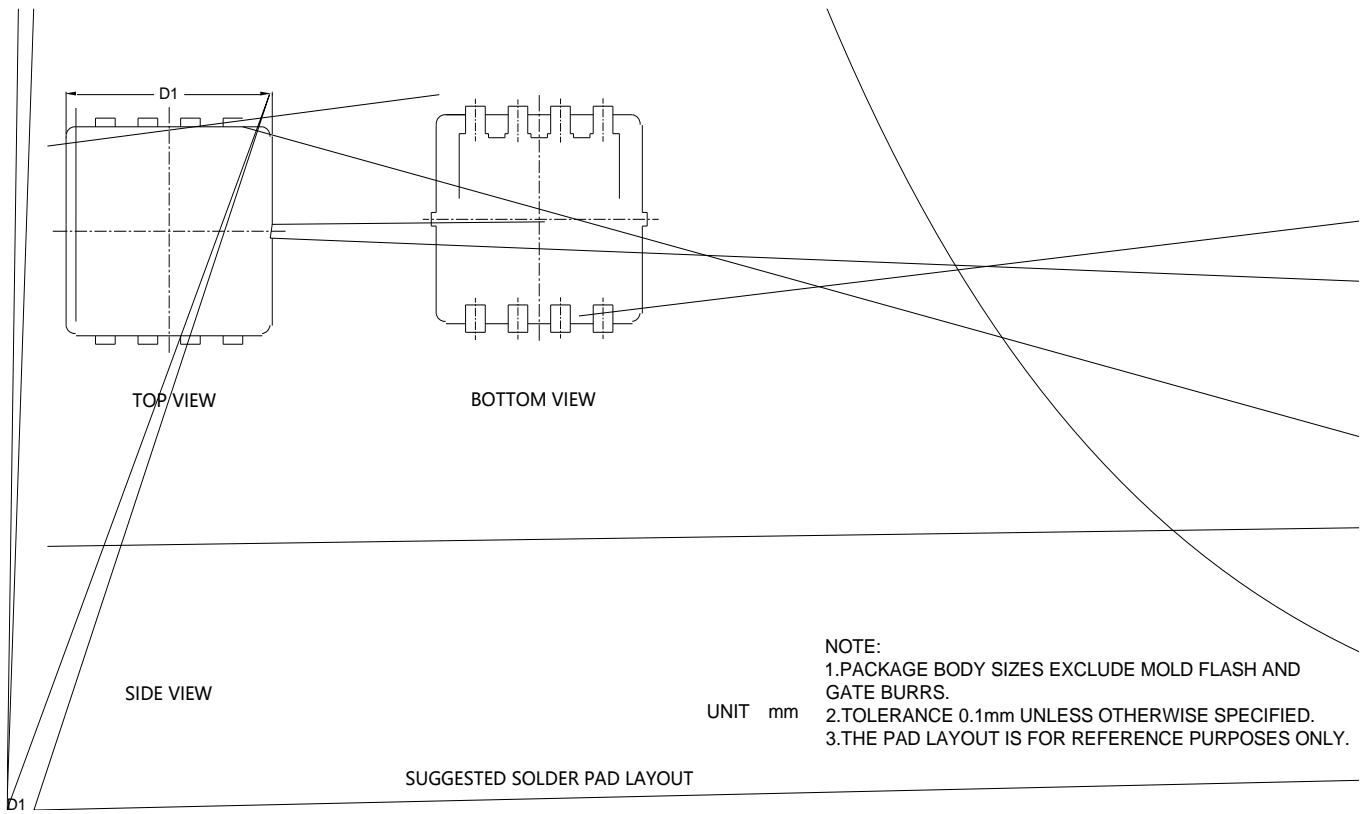


Figure 14. Safe Operation Area



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## PDFN3333-8L-B-0.75MM Package information





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## Disclaimer

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